

Amendments to the Specification

Kindly amend the specification as follows:

Page 1, between the title and the heading "**BACKGROUND OF THE INVENTION**", insert

--CROSS REFERENCE TO RELATED APPLICATIONS

This is a divisional application of application Serial No. 09/544,172, filed April 6, 2000, which is hereby incorporated by reference in its entirety for all purposes.--

Please replace the paragraph beginning on page 2, line 2 with the following amended paragraph:

In one such method, as illustrated in Fig. 11, with the circuit forming surface [[82]] 82a of the semiconductor element 82 and the wiring forming surface 80a of the mount substrate 80 opposing one another, the substrate side electrodes of the mount substrate 80 and the element side electrodes of the semiconductor element 82 are joined together by solder bumps 85. The space between the circuit forming surface 82a of the semiconductor element 82 and the wiring forming surface 80a of the mount substrate 80 is sealed by the sealing resin 81 which is insulative. As shown in Fig. 11, because no wire is used in a semiconductor device obtained by this method, a semiconductor device having a thinner package can be obtained.

Replace the paragraph beginning on pag 13, line 5 with the following

amended paragraph:

This semiconductor device can be formed in the following manner. First, conductive filaments 20 (see Fig. 3B), each of which is formed by bundling conductive carbon fibers 22, and insulative filaments 24, each of which is formed by bundling fibers formed from an insulative material such as glass, are used as the warp threads. The conductive filaments ~~[[24]]~~ 20 are also used as the weft threads. These filaments 20, 24 are woven into a plain weave so as to form the cross base material 30 illustrated in Fig. 3A. The cross base material 30 is a structural element of a cross substrate 10a which will be described later. The conductive filaments 20 woven into the cross base material 30 serve as wires.

Replace the paragraph beginning on page 15, line 8 with the following

amended paragraph:

As a result, the dimensions of the obtained semiconductor device are substantially the same as the dimensions of the semiconductor element 12. The thickness of the semiconductor device varies in accordance with the amount of the semiconductor element 12 within the sealing resin 11. (Namely, if the amount of the semiconductor element 12 within the sealing resin 11 is small, the thickness of the semiconductor device is substantially the same as the total of the thickness of the semiconductor element 12 and the thickness of the cross substrate ~~[[10]]~~ 10a. If the

amount of the semiconductor element 12 within the sealing resin 11 is great, the thickness of the semiconductor device is smaller than the total of the thickness of the semiconductor element 12 and the thickness of the cross substrate [[10]] 10a.) At the most, the thickness of the semiconductor device is the same as the total of the thickness of the semiconductor element 12 and the thickness of the cross substrate [[10]] 10a. Thus, a semiconductor device which is much thinner than conventional semiconductor devices can be obtained.